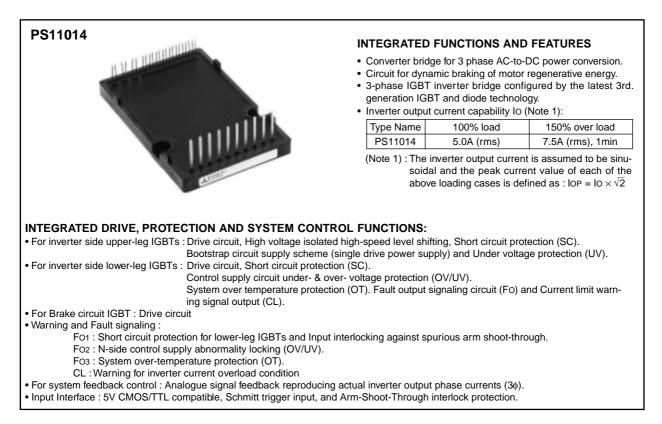
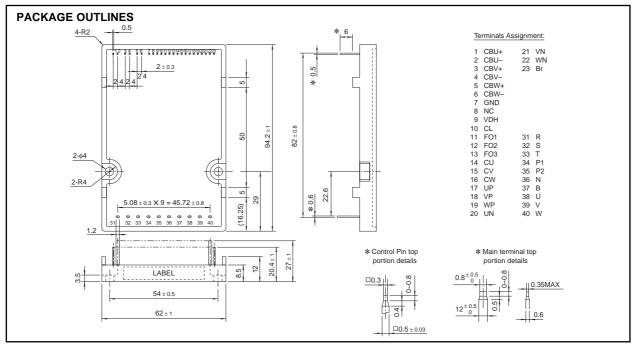
PS11014 FLAT-BASE TYPE INSULATED TYPE



### APPLICATION

Acoustic noise-less 0.75kW/AC200V class 3 phase inverter and other motor control applications

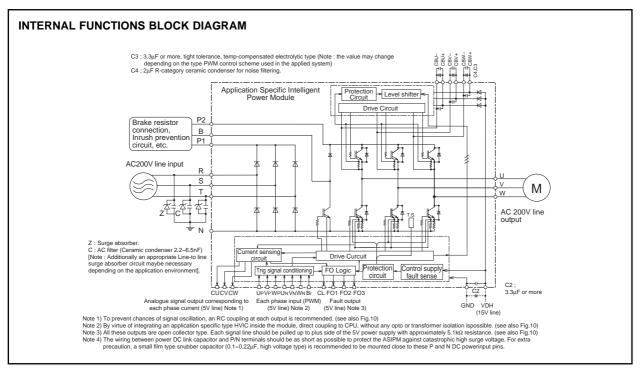


(Fig. 1)



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### MAXIMUM RATINGS (Tj = 25°C) INVERTER PART (Including Brake Part)

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P2-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P2-N, Surge-value	500	V
VP or VN	Each output IGBT collector-emitter static voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	N, 600	
VP(S) or VN(S)	Each output IGBT collector-emitter switching surge voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	W, 600	
±IC(±ICP)	Each output IGBT collector current	Tc = 25°C	±15 (±30)	Α
IC(ICP)	Brake IGBT collector current		4 (8)	Α
IF(IFP)	Brake diode anode current	Note: "( )" means IC peak value	4 (8)	Α

### CONVERTER PART

Symbol	Item	Condition	Ratings	Unit
Vrrm	Repetitive peak reverse voltage		800	V
Ea	Recommended AC input voltage		220	V
lo	DC output current	3¢ rectifying circuit	25	Α
IFSM	Surge (non-repetitive) forward current	1 cycle at 60Hz, peak value non-repetitive	196	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	Value for one cycle of surge current	160	A <sup>2</sup> s

### CONTROL PART

Symbol	Item	Condition	Ratings	Unit
Vdh, Vdb	Supply voltage	Applied between VDH-GND, CBU+-CBU–, CBV+-CBV–, CBW+-CBW–	20	V
VCIN	Input signal voltage	Applied between UP $\cdot$ VP $\cdot$ WP $\cdot$ UN $\cdot$ VN $\cdot$ WN $\cdot$ Br-GND	-0.5 ~ 7.5	V
VFO	Fault output supply voltage	Applied between F01 · F02 · F03-GND	-0.5 ~ 7	V
IFO	Fault output current	Sink current of F01 · F02 · F03	15	mA
VCL	Current-limit warning (CL) output voltage	Applied between CL-GND	-0.5 ~ 7	V
ICL	CL output current	Sink current of CL	15	mA
Ico	Analogue current signal output current	Sink current of CU · CV · CW	±1	mA



## PS11014

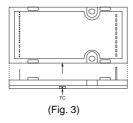
FLAT-BASE TYPE INSULATED TYPE

### TOTAL SYSTEM

Symbol	Item	Condition	Ratings	Unit
Tj	Junction temperature	(Note 2)	-20 ~ +125	°C
Tstg	Storage temperature	—	-40 ~ +125	°C
Тс	Module case operating temperature	(Fig. 3)	-20 ~ +100	°C
Viso	Isolation voltage	60 Hz sinusoidal AC applied between all terminals and the base plate for 1 minute.	2500	Vrms
_	Mounting torque	Mounting screw: M3.5	0.78 ~ 1.27	kg∙cm

Note 2) The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the ASIPM to ensure safe operation. However, these power elements can endure junction temperature as high as 150°C instantaneously. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is requested to be provided before use.

### CASE TEMPERATURE MEASUREMENT POINT (3mm from the base surface)



### THERMAL RESISTANCE

Symbol	ltere	Condition		Ratings		
	Item	Condition	Min.	Тур.	Max.	Unit
Rth(j-c)Q		Inverter IGBT (1/6)	—	—	2.8	°C/W
Rth(j-c)F	Junction to case Thermal Resistance	Inverter FWDi (1/6)	—	—	3.9	°C/W
Rth(j-c)QB		Brake IGBT	_	_	5.8	°C/W
Rth(j-c)FB		Brake FWDi	—	—	6.0	°C/W
Rth(j-c)FR		Converter Di (1/6)	_	_	4.3	°C/W
Rth(c-f)	Contact Thermal Resistance	Case to fin, thermal grease applied (1 Module)	_	_	0.044	°C/W

### ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Symbol	Item	Condition		Ratings			
Symbol		Condition		Тур.	Max.	Unit	
VCE(sat)	Collector-emitter saturation voltage	VDH = VDB = 15V, Input = ON, Tj = 25°C, IC = 15A	_	_	2.9	V	
VEC	FWDi forward voltage	Tj = $25^{\circ}$ C, IC = $-15$ A, Input = OFF	—	—	2.9	V	
VCE(sat)Br	Brake IGBT Collector-emitter saturation voltage	VDH = 15V, Input = ON, Tj = 25°C, IC = 4A		_	3.5	V	
VFBr	Brake diode forward voltage	Tj = 25°C, IF = 4A, Input = OFF		—	2.9	V	
IRRM	Converter diode reverse current	VR = VRRM, Tj = 125°C	—	—	8	mA	
Vfr	Converter diode voltage	Tj = 25°C, IF = 10A	—	—	1.5	V	
ton		1/2 Bridge inductive load, Input = ON	0.3	0.6	1.5	μs	
tc(on)	Switching times	Vcc = 300V, lc = 15A, Tj = 125°C	_	0.2	0.6	μs	
toff		VDH = 15V, VDB = 15V	_	1.1	1.8	μs	
tc(off)		Note : ton, toff include delay time of the internal control	_	0.4	1.0	μs	
trr	FWD reverse recovery time	circuit	—	0.1	—	μs	
	Short circuit endurance	Vcc $\leq$ 400V, Input = ON (one-shot)	No destruction Fo output by protection operation				
	(Output, Arm, and Load,	Tj = 125°C start				ration	
	Short Circuit Modes)	$13.5V \le VDH = VDB \le 16.5V$					
		$Vcc \le 400V$ , $Tj \le 125^{\circ}C$ ,	No destruction				
	Switching SOA	Ic < IOL(CL) operation level, Input = ON	<ul><li>No protecting operation</li><li>No Fo output</li></ul>		ration		
		$13.5V \le VDH = VDB \le 16.5V$					



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### **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Item		Condition		Ratings		
	Conc	ation	Min.	Тур.	Max.	Unit
	VDH = 15V, VCIN = 5V		—	—	150	mA
			0.8	1.4	2.0	V
			2.5	3.0	4.0	V
Input pull-up resistor		it terminal-VDH	—	150	—	kΩ
PWM input frequency Allowable input on-pulse width		;	2	—	20	kHz
	VDH = 15V, TC = -20°C	( )	1		500	μs
me for	Relates to corresponding (Except brake part) Tc = -		2.2	_	_	μs
	Relates to corresponding	input (Except brake part)	—	65	100	ns
	Ic = 0A	Vdh = 15V	1.87	2.27	2.57	V
Analogue signal linearity with output current		$Tc = -20^{\circ}C \sim +100^{\circ}C$	0.77	1.17	1.47	V
		(Fig. 4)	2.97	3.37	3.67	V
ature	VDH = 15V, TC = -20°C ~ +100°C			15	_	mV
- Analogue signal output voltage limit Ic > IoP(200%), VDH = 15V		Ic > IOP(200%), VDH = 15V	_	_	0.7	V
		(Fig. 4)	4.0	_	_	V
r variation	Vco-Vc±(200%)		_	1.1	_	V
Analogue signal data hold accuracy		0μs data hold period (Fig. 5)	-5	_	5	%
	After input signal trigge	r point (Fig. 8)	_	3	_	μs
ation level	VDH =15V, TC = -20°C		14.05	17.30	20.80	Α
dle	-	. ,	_	_	1	μA
Active	Open collector output		_	1	_	mA
evel	Tj = 25°C	(Fig. 7) (Note 5)	23.2	43.0	62.0	Α
rip level			100	110	120	°C
Reset level	VDH =15V			90	_	°C
rip level			11.05	12.00	12.75	V
Reset level			11.55	12.50	13.25	V
rip level			18.00	19.20	20.15	V
Reset level	$Tc = -20^{\circ}C \sim +100^{\circ}C$		16.50	17.50	18.65	V
rip level	Tj ≤ 125°C		10.0	11.0	12.0	V
Reset level			10.5	11.5	12.5	V
ilter time				10	_	μs
dle			_	_	1	μA
ctive	Open collector output			1	<u> </u>	mA
lb	е		e Open collector output	e	e	e Open collector output

(Note 3) : (a) Allowable minimum input on-pulse width : This item applies to P-side circuit only.

(b) Allowable maximum input on-pulse width : This item applies to both P-side and N-side circuits excluding the brake circuit. (Note4) : CL output : The "current limit warning (CL) operation circuit outputs warning signal whenever the arm current exceeds this limit. The

circuit is reset automatically by the next input signal and thus, it operates on a pulse-by-pulse scheme.

(Note5): The short circuit protection works instantaneously when a high short circuit current flows through an internal IGBT rising up momentarily. The protection function is, thus meant primarily to protect the ASIPM against short circuit distraction. Therefore, this function is not recommended to be used for any system load current regulation or any over load control as this might, cause a failure due to excessive temperature rise. Instead, the analogue current output feature or the over load warning feature (CL) should be appropriately used for such current regulation or over load control operation. In other words, the PWM signals to the ASIPM should be shut down, in principle, and not to be restarted before the junction temperature would recover to normal, as soon as a fault is feed back from its Fo1 pin of the ASIPM indicating a short circuit situation.

### **RECOMMENDED CONDITIONS**

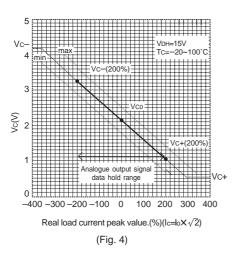
Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied across P2-N terminals	400 (max.)	V
Vdh, Vdb	Control supply voltage	Applied between VDH-GND, CBU+-CBU–, CBV+-CBV–, CBW+-CBW–	15±1.5	V
$\Delta {\rm Vdh}, \Delta {\rm Vdb}$	Supply voltage ripple		±1 (max.)	V/µs
VCIN(on)	Input on voltage		0 ~ 0.3	V
VCIN(off)	Input off voltage		4.8 ~ 5.0	V
fpwm	PWM Input frequency	Using application circuit	2 ~ 20	kHz
tdead	Arm shoot-through blocking time	Using application circuit	2.2 (min.)	μs



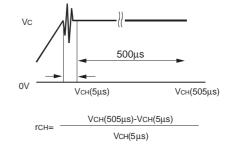
### PS11014 FLAT-BASE TYPE

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### Fig. 4 OUTPUT CURRENT ANALOGUE SIGNALING LINEARITY

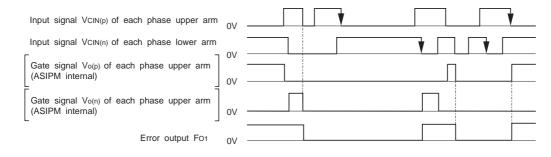


### Fig. 5 OUTPUT CURRENT ANALOGUE SIGNALING "DATA HOLD" DEFINITION



Note ; Ringing happens around the point where the signal output voltage changes state from "analogue" to "data hold" due to test circuit arrangement and instrumentational trouble. Therefore, the rate of change is measured at a 5 µs delayed point.

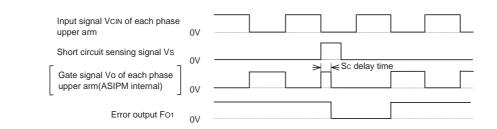
#### Fig. 6 INPUT INTERLOCK OPERATION TIMING CHART



Note : Input interlock protection circuit ; It is operated when the input signals for any upper-arm / lower-arm pair of a phase are simultaneously in "LOW" level.

By this interlocking, both upper and lower IGBTs of this mal-triggered phase are cut off, and "Fo" signal is outputted. After an "input interlock" operation the circuit is latched. The "Fo" is reset by the high-to-low going edge of either an upper-leg, or a lower-leg input, whichever comes in later.

### Fig. 7 TIMING CHART AND SHORT CIRCUIT PROTECTION OPERATION

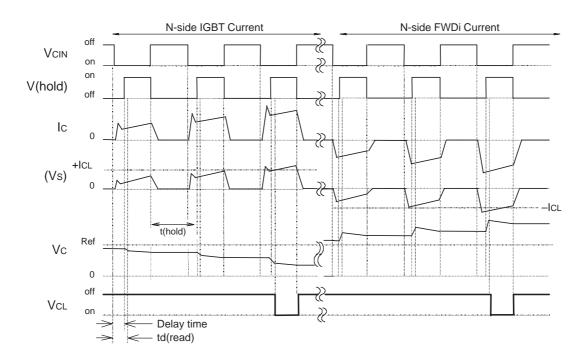


Note : Short circuit protection operation. The protection operates with "Fo" flag and reset on a pulse-by-pulse scheme. The protection by gate shutdown is given only to the IGBT that senses an overload (excluding the IGBT for the "Brake").



### PS11014 FLAT-BASE TYPE

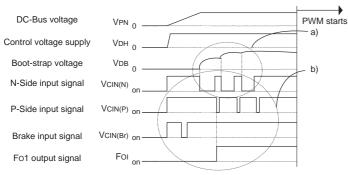
INSULATED TYPE



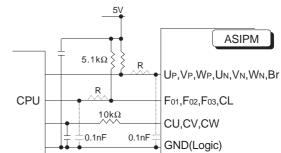
### Fig. 8 INVERTER OUTPUT ANALOGUE CURRENT SENSING AND SIGNALING TIMING CHART

### Fig. 9 START-UP SEQUENCE

Normally at start-up, Fo and CL output signals will be pulled-up High to Supply voltage (OFF level); however, Fo1 output may fall to Low (ON) level at the instant of the first ON input pulse to an N-Side IGBT. This can happen particularly when the boot-strap capacitor is of large size. Fo1 resetting sequence (together with the boot-strap charging sequence) is explained in the following graph



### Fig. 10 RECOMMENDED I/O INTERFACE CIRCUIT



### a) Boot-strap charging scheme :

Apply a train of short ON pulses at all N-IGBT input pins for adequate charging (pulse width = approx. 20µs number of pulses =10 ~ 500 depending on the boot-strap capacitor size)

#### b) Fo1 resetting sequence:

Apply ON signals to the following input pins : Br  $\rightarrow$  Un/Vn/Wn  $\rightarrow$  Up/Vp/Wp in that order.

